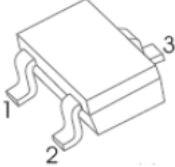


TRANSISTOR (PNP)	SOT-323 Plastic-Encapsulate Transistors
<p>SOT-323</p>  <p>1. BASE 2. EMITTER 3. COLLECTOR</p> <p>Marking :K3F</p>	<p>Features</p> <ul style="list-style-type: none"> • Epitaxial planar die construction • Complementary PNP Type available(MMST2222A)

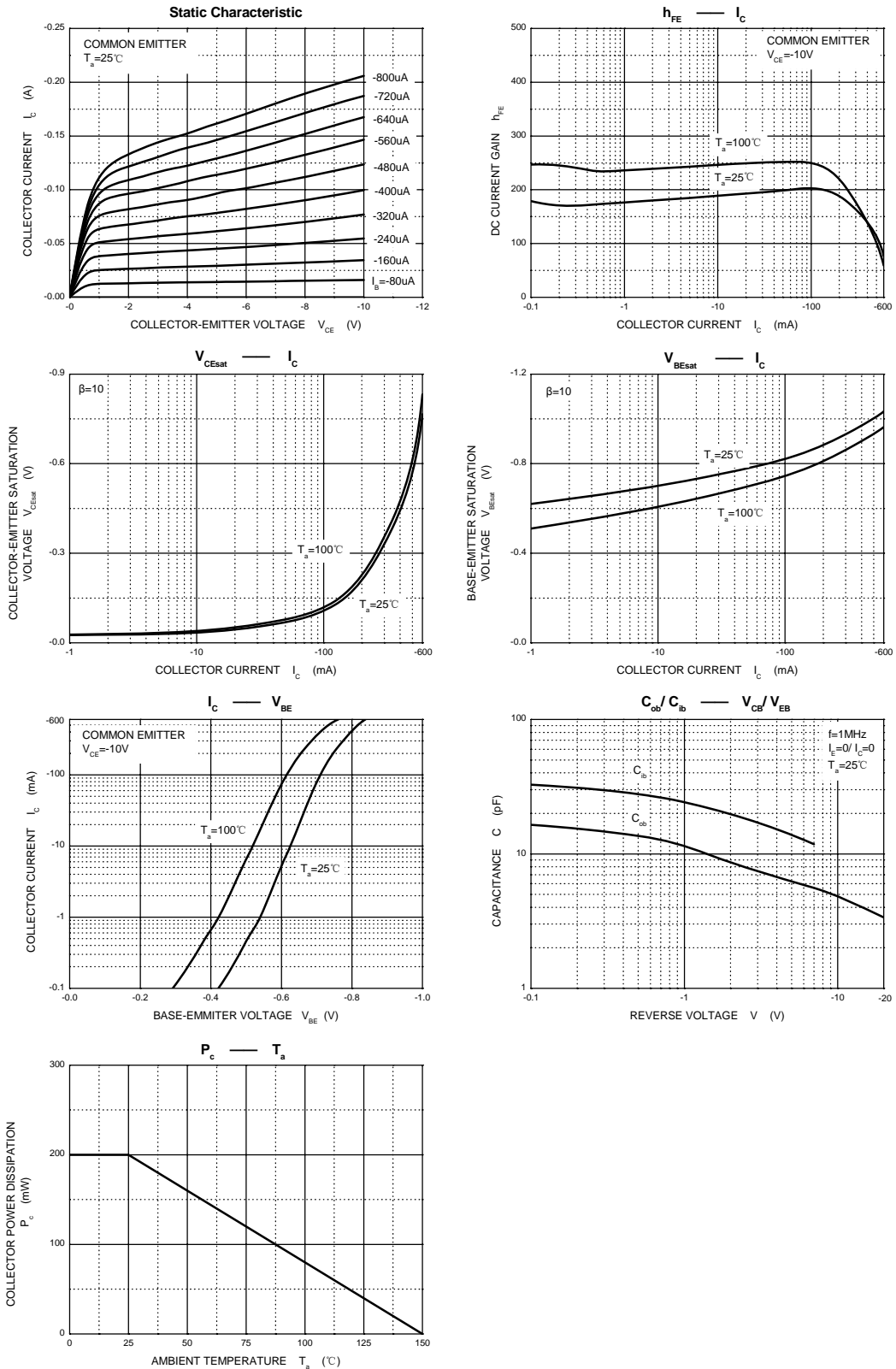
MAXIMUM RATINGS(T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.6	A
P _C	Collector Dissipation	0.2	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55 to +150	°C

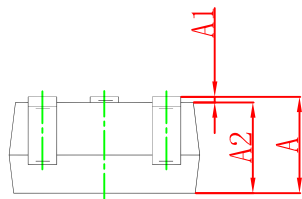
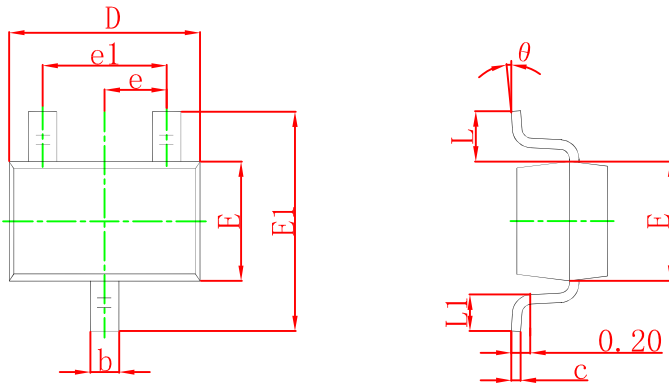
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-50V, I _E =0			-100	nA
Collector cut-off current	I _{CES}	V _{CB} =-30V, I _B =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V, I _C =0			-100	nA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _C =-0.1mA	75			
	h _{FE(2)}	V _{CE} =-10V, I _C =-1mA	100			
	h _{FE(3)}	V _{CE} =-10V, I _C =-10mA	100			
	h _{FE(4)}	V _{CE} =-10V, I _C =-150mA	100		300	
	h _{FE(5)}	V _{CE} =-10V, I _C =-500mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-150mA, I _B =-15mA			-0.4	V
	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-1.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-150mA, I _B =-15mA	-0.6		-1.3	V
	V _{BE(sat)}	I _C =-500mA, I _B =-50mA			-2.6	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-50mA, f=100MHz	200			MHz
Output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=0.1MHz			8	pF
Input capacitance	C _{ib}	V _{EB} =-2V, I _C =0, f=0.1MHz			30	pF
Delay time	t _d	V _{CC} =-30V, V _{BE(off)} =-1.5V, I _C =-150mA			10	ns
Rise time	t _r	I _{B1} =-15mA			40	ns
Storage time	t _s	V _{CC} =-30V, I _C =-150mA, I _{B1} =-I _{B2} =-15mA			80	ns
Fall time	t _f				30	ns

Typical Characteristics

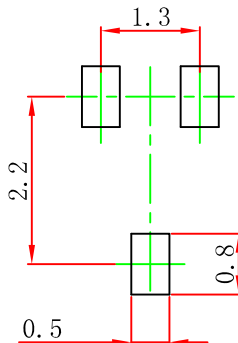


SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-323 Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)